# **General Purpose Transistors**

# **NPN Silicon**

#### **Features**

- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector-Emitter Voltage  MMBT2222L  MMBT2222AL, SMMBT2222AL	V <sub>CEO</sub>	30 40	Vdc
Collector – Base Voltage  MMBT2222L  MMBT2222AL, SMMBT2222AL	V <sub>CBO</sub>	60 75	Vdc
Emitter-Base Voltage  MMBT2222L  MMBT2222AL, SMMBT2222AL	V <sub>EBO</sub>	5.0 6.0	Vdc
Collector Current – Continuous	Ic	600	mAdc
Collector Current – Peak (Note 3)	I <sub>CM</sub>	1100	mAdc

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate (Note 2) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

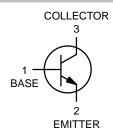
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1.  $FR-5 = 1.0 \times 0.75 \times 0.062$  in.
- 2. Alumina =  $0.4 \times 0.3 \times 0.024$  in. 99.5% alumina.
- 3. Reference SOA curve.



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SOT-23 CASE 318 STYLE 6

### **MARKING DIAGRAM**



xxx = 1P or M1B M = Date Code\* • = Pb-Free Package

(Note: Microdot may be in either location)
\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

## ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

# **ELECTRICAL CHARACTERISTICS** ( $T_A = 25$ °C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage (I <sub>C</sub> = 10 mAdc,	I <sub>B</sub> = 0) MMBT2222 MMBT2222A		30 40	_ _	Vdc
Collector – Base Breakdown Voltage ( $I_C = 10 \mu Adc, I_E$	V <sub>(BR)CBO</sub>	60 75	_ _	Vdc	
Emitter – Base Breakdown Voltage ( $I_E$ = 10 $\mu$ Adc, $I_C$ =	0) MMBT2222 MMBT2222A	(511)250	5.0 6.0	- -	Vdc
Collector Cutoff Current (V <sub>CE</sub> = 60 Vdc, V <sub>EB(off)</sub> = 3.0 Vdc)	MMBT2222A, SMMBT2222A	I <sub>CEX</sub>	-	10	nAdc
Collector Cutoff Current ( $V_{CB} = 50 \text{ Vdc}$ , $I_{E} = 0$ ) ( $V_{CB} = 60 \text{ Vdc}$ , $I_{E} = 0$ ) ( $V_{CB} = 50 \text{ Vdc}$ , $I_{E} = 0$ , $T_{A} = 125^{\circ}\text{C}$ ) ( $V_{CB} = 60 \text{ Vdc}$ , $I_{E} = 0$ , $T_{A} = 125^{\circ}\text{C}$ )	MMBT2222A MMBT2222A, SMMBT2222A MMBT2222 MMBT2222A, SMMBT2222A	A 2	- - - -	0.01 0.01 10 10	μAdc
Emitter Cutoff Current (V <sub>EB</sub> = 3.0 Vdc, I <sub>C</sub> = 0)	MMBT2222A, SMMBT2222A	I <sub>EBO</sub>	-	100	nAdc
Base Cutoff Current (V <sub>CE</sub> = 60 Vdc, V <sub>EB(off)</sub> = 3.0 Vdc)	MMBT2222A, SMMBT2222A	A I <sub>BL</sub>	-	20	nAdc
ON CHARACTERISTICS			•	•	•
DC Current Gain $ \begin{array}{l} (I_C=0.1 \text{ mAdc, } V_{CE}=10 \text{ Vdc}) \\ (I_C=1.0 \text{ mAdc, } V_{CE}=10 \text{ Vdc}) \\ (I_C=10 \text{ mAdc, } V_{CE}=10 \text{ Vdc}) \\ (I_C=10 \text{ mAdc, } V_{CE}=10 \text{ Vdc}) \\ (I_C=10 \text{ mAdc, } V_{CE}=10 \text{ Vdc, } T_A=-55^{\circ}\text{C}) \\ (I_C=150 \text{ mAdc, } V_{CE}=10 \text{ Vdc) (Note 4)} \\ (I_C=150 \text{ mAdc, } V_{CE}=1.0 \text{ Vdc) (Note 4)} \\ (I_C=500 \text{ mAdc, } V_{CE}=10 \text{ Vdc) (Note 4)} \\ \end{array} $	MMBT2222A only MMBT2222 MMBT2222A, SMMBT2222A	2	35 50 75 35 100 50 30 40	- - - 300 - -	-
Collector – Emitter Saturation Voltage (Note 4) (I <sub>C</sub> = 150 mAdc, I <sub>B</sub> = 15 mAdc)	MMBT2222 MMBT2222A, SMMBT2222A		_ _	0.4 0.3	Vdc
$(I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc})$	MMBT2222 MMBT2222A, SMMBT2222A		- -	1.6 1.0	
Base – Emitter Saturation Voltage (Note 4) (I <sub>C</sub> = 150 mAdc, I <sub>B</sub> = 15 mAdc)	MMBT2222 MMBT2222A, SMMBT2222A		_ 0.6	1.3 1.2	Vdc
$(I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc})$	MMBT2222 MMBT2222A, SMMBT2222A		- -	2.6 2.0	
SMALL-SIGNAL CHARACTERISTICS			-	-	-
Current – Gain – Bandwidth Product (Note 5) (I <sub>C</sub> = 20 mAdc, V <sub>CE</sub> = 20 Vdc, f = 100 MHz)	MMBT2222 MMBT2222A, SMMBT2222A		250 300	- -	MHz
Output Capacitance (V <sub>CB</sub> = 10 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)		C <sub>obo</sub>	-	8.0	pF
Input Capacitance (V <sub>EB</sub> = 0.5 Vdc, I <sub>C</sub> = 0, f = 1.0 MHz)	MMBT2222A, SMMBT2222A		_ _	30 25	pF
Input Impedance (I <sub>C</sub> = 1.0 mAdc, $V_{CE}$ = 10 Vdc, f = 1.0 kHz) (I <sub>C</sub> = 10 mAdc, $V_{CE}$ = 10 Vdc, f = 1.0 kHz)	MMBT2222A, SMMBT2222A MMBT2222A, SMMBT2222A		2.0 0.25	8.0 1.25	kΩ
Voltage Feedback Ratio ( $I_C = 1.0 \text{ mAdc}$ , $V_{CE} = 10 \text{ Vdc}$ , $f = 1.0 \text{ kHz}$ ) ( $I_C = 10 \text{ mAdc}$ , $V_{CE} = 10 \text{ Vdc}$ , $f = 1.0 \text{ kHz}$ )	MMBT2222A, SMMBT2222A MMBT2222A, SMMBT2222A		_ _	8.0 4.0	X 10 <sup>-4</sup>
Small – Signal Current Gain ( $I_C = 1.0 \text{ mAdc}$ , $V_{CE} = 10 \text{ Vdc}$ , $f = 1.0 \text{ kHz}$ ) ( $I_C = 10 \text{ mAdc}$ , $V_{CE} = 10 \text{ Vdc}$ , $f = 1.0 \text{ kHz}$ )	MMBT2222A, SMMBT2222A MMBT2222A, SMMBT2222A		50 75	300 375	_

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

ELECTRICAL CHARACTERISTICS (	TA = 25 C driless office wise noted)		_		
Characteristic			Min	Max	Unit
SMALL-SIGNAL CHARACTERISTICS					
Output Admittance			5.0 25	35 200	μmhos
Collector Base Time Constant (I <sub>E</sub> = 20 mAdc, V <sub>CB</sub> = 20 Vdc, f = 31.8 MHz) MMBT2222A, SMMBT2222A			-	150	ps
Noise Figure (I <sub>C</sub> = 100 $\mu$ Adc, V <sub>CE</sub> = 10 Vdc, R <sub>S</sub> = 1.0 k $\Omega$ , f = 1.0 kHz) MMBT2222A, SMMBT2222A			-	4.0	dB
SWITCHING CHARACTERISTICS (MMBT	2222A only)				
Delay Time	$(V_{CC} = 30 \text{ Vdc}, V_{BE(off)} = -0.5 \text{ Vdc},$	t <sub>d</sub>	_	10	
Rise Time	$(V_{CC} = 30 \text{ Vdc}, V_{BE(off)} = -0.5 \text{ Vdc}, \\ I_{C} = 150 \text{ mAdc}, I_{B1} = 15 \text{ mAdc})$	t <sub>r</sub>	-	25	ns
Storage Time	(V <sub>CC</sub> = 30 Vdc, I <sub>C</sub> = 150 mAdc,	t <sub>s</sub>	-	225	200
Fall Time	$I_{B1} = I_{B2} = 15 \text{ mAdc}$	t <sub>f</sub>	_	60	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- 4. Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%.
- 5. f<sub>T</sub> is defined as the frequency at which |h<sub>fe</sub>| extrapolates to unity.

## **SWITCHING TIME EQUIVALENT TEST CIRCUITS**

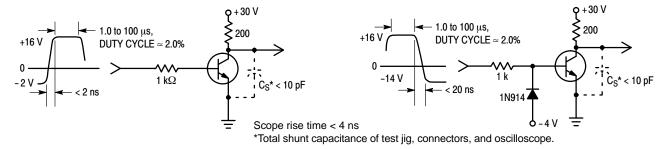


Figure 1. Turn-On Time

Figure 2. Turn-Off Time

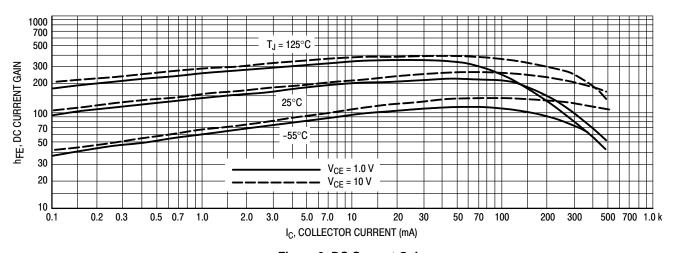


Figure 3. DC Current Gain

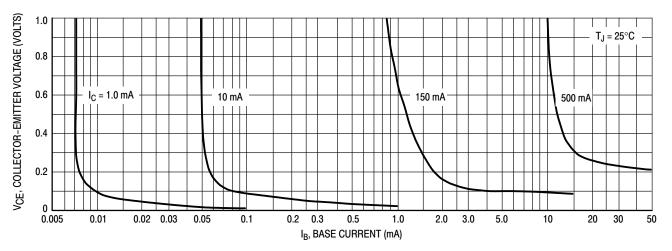


Figure 4. Collector Saturation Region

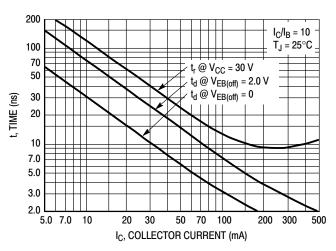


Figure 5. Turn-On Time

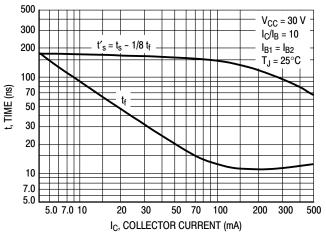


Figure 6. Turn-Off Time

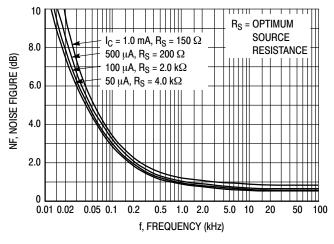


Figure 7. Frequency Effects

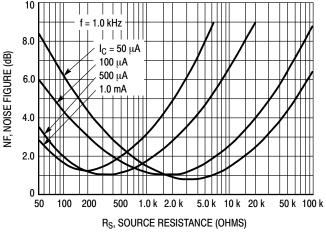
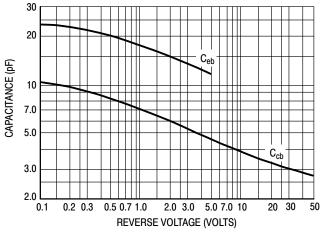


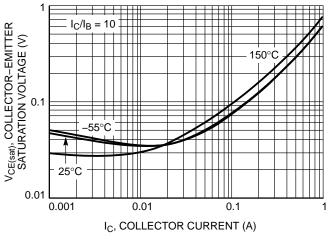
Figure 8. Source Resistance Effects



f<sub>T</sub>, CURRENT-GAIN BANDWIDTH PRODUCT (MHz) 500 V<sub>CE</sub> = 20 V  $T_J = 25^{\circ}C$ 300 200 100 70 50 70 100 1.0 2.0 3.0 5.0 7.0 20 50 IC, COLLECTOR CURRENT (mA)

Figure 9. Capacitances

Figure 10. Current-Gain Bandwidth Product



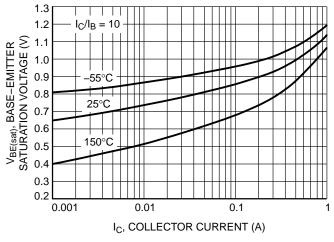
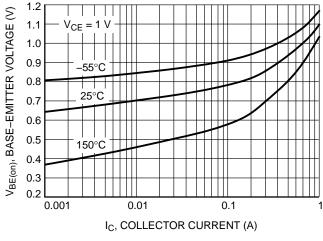


Figure 11. Collector Emitter Saturation Voltage vs. Collector Current

Figure 12. Base Emitter Saturation Voltage vs.
Collector Current



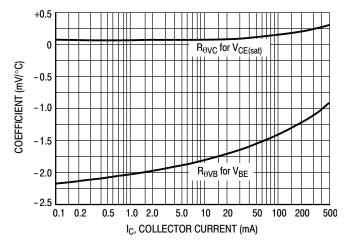


Figure 13. Base Emitter Voltage vs. Collector Current

**Figure 14. Temperature Coefficients** 

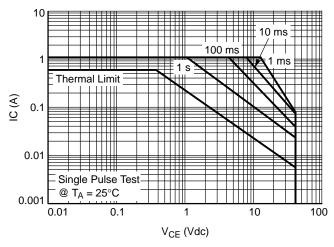


Figure 15. Safe Operating Area

#### **ORDERING INFORMATION**

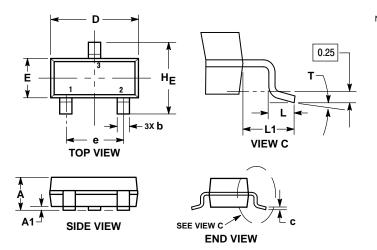
Device	Specific Marking Code	Package	Shipping <sup>†</sup>	
MMBT2222LT1G	M1B	SOT-23 (Pb-Free)	3000 / Tape & Reel	
MMBT2222ALT1G, SMMBT2222ALT1G	1P	SOT-23 (Pb-Free)	3000 / Tape & Reel	
MMBT2222LT3G	M1B	SOT-23 (Pb-Free)	10,000 / Tape & Reel	
MMBT2222ALT3G, SMMBT2222ALT3G	1P	SOT-23 (Pb-Free)	10,000 / Tape & Reel	

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
\*S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP

Capable.

#### PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AR** 



#### NOTES:

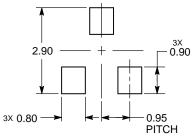
- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
  MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
  DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH.
- PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0°		10°	0°	-	10°

#### STYLE 6:

- PIN 1. 2. BASE
  - **EMITTER**
  - COLLECTOR

#### **RECOMMENDED** SOLDERING FOOTPRINT\*



**DIMENSIONS: MILLIMETERS** 

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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